ACT108-600D AC Thyristor power switch Rev. 02 — 27 December 2010



Product data sheet

1. **Product profile**

1.1 General description

AC Thyristor power switch in a SOT54 plastic package with self-protective capabilities against low and high energy transients

1.2 Features and benefits

- Exclusive negative gate triggering
- Full cycle AC conduction
- High noise immunity
- Remote gate separates the gate driver from the effects of the load current
- Safe clamping of low energy over-voltage transients
- Self-protective turn-on during high energy voltage transients
- Very sensitive gate for lowest gate trigger current

1.3 Applications

- Fan motor circuits
- Lower-power highly inductive, resistive and safety loads
- Pump motor circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD- G-;} $ $T_j = 25 \text{ °C}$	0.5	-	5	mA
		$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G-;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 6}}{\text{ or } 100 \text{ mA; LD+ G-;}}$	0.5	-	5	mA
I _{T(RMS)}	RMS on-state current	full sine wave; T _{lead} ≤ 71 °C; see <u>Figure 2</u>	-	-	8.0	Α
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 402 V; T _j = 125 °C; gate open circuit; exponential waveform; see <u>Figure 10</u>	300	-	-	V/µs
V_{CL}	clamping voltage	I_{CL} = 100 μ A; t_p = 1 ms; $T_i \le$ 125 °C; see Figure 13	650	-	-	V



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 100 \text{ mA;}$ $T_j = 25 \text{ °C}$	-	-	0.9	V
V_{PP}	peak pulse voltage	$T_j = 25$ °C; non-repetitive, off-state; see Figure 1	-	-	2	kV
V_{T}	on-state voltage	I _T = 1.1 A; see <u>Figure 9</u>	-	-	1.3	V

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	CM	common		
2	G	gate		LD
3	LD	load		G — CM 001aaj924
			SOT54 (TO-92)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
ACT108-600D	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{lead} ≤ 71 °C; see <u>Figure 2</u>	-	0.8	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	8.8	Α
		full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 20 \text{ms}$; see <u>Figure 3</u> ; see <u>Figure 4</u>	-	8	Α
l ² t	I2t for fusing	t _p = 10 ms; sine-wave pulse	-	0.32	A ² s
dI _T /dt	rate of rise of on-state current	$I_T = 1 \text{ A}$; $I_G = 10 \text{ mA}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	50	A/µs
I_{GM}	peak gate current	t = 20 μs	-	1	Α
V_{GM}	peak gate voltage	positive applied gate voltage	-	15	V
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C
V_{PP}	peak pulse voltage	T _j = 25 °C; non-repetitive, off-state; see Figure 1	-	2	kV

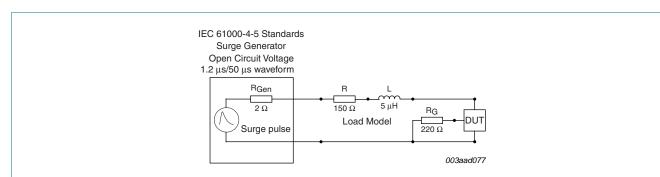


Fig 1. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

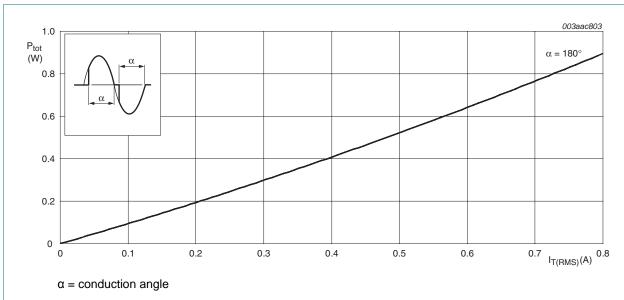


Fig 2. Total power dissipation as a function of RMS on-state current; maximum values

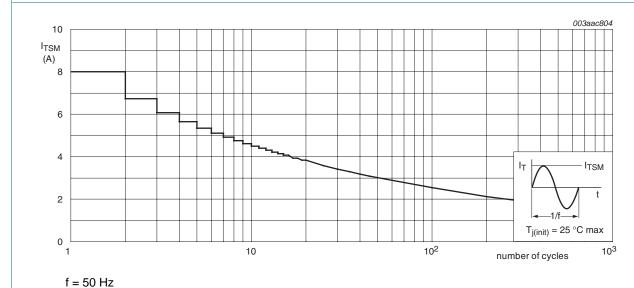
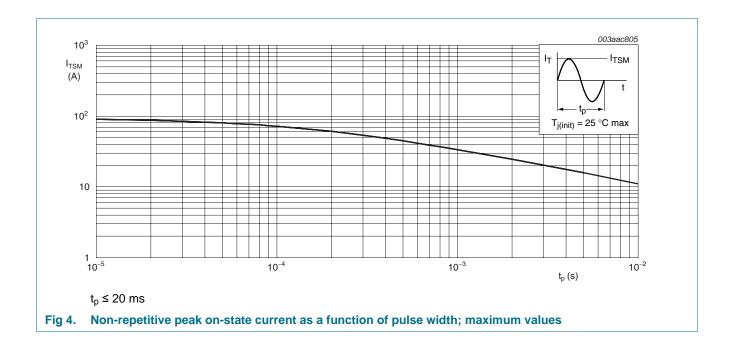


Fig 3. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance from junction to lead	full cycle with heatsink compound; see Figure 5	-	-	60	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	full cycle; printed-circuit board mounted; lead length 4 mm	-	150	-	K/W

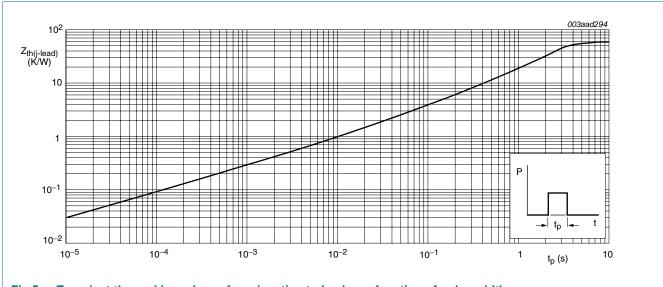
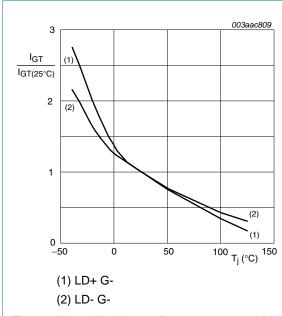


Fig 5. Transient thermal impedance from junction to lead as a function of pulse width

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 100 \text{ mA}; \text{LD- G-};$ $T_j = 25 \text{ °C}$	0.5	-	5	mA
		$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G-;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 6}}{\text{C}}$	0.5	-	5	mA
IL	latching current	$V_D = 12 \text{ V; } I_G = 12 \text{ mA; } T_j = 25 \text{ °C;}$ see Figure 7	-	-	25	mA
I _H	holding current	$V_D = 12 \text{ V; } T_j = 25 \text{ °C; see } \frac{\text{Figure 8}}{\text{ or } 100 \text{ J}}$	-	-	20	mA
V_{T}	on-state voltage	I _T = 1.1 A; see <u>Figure 9</u>	-	-	1.3	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 100 \text{ mA}; T_j \le 125 \text{ °C}$	0.15	-	-	V
		$V_D = 12 \text{ V}; I_T = 100 \text{ mA}; T_j = 25 \text{ °C}$	-	-	0.9	V
I _D	off-state current	V _D = 600 V; T _j ≤ 25 °C	-	-	2	μΑ
		V _D = 600 V; T _j ≤ 125 °C	-	-	0.2	mA
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; gate open circuit; exponential waveform; see Figure 10	300	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}; T_j = 125 ^{\circ}\text{C};$ $I_{T(RMS)} = 1 \text{ A}; dV_{com}/dt = 15 \text{ V/}\mu\text{s};$ gate open circuit; see Figure 11; see Figure 12	0.15	-	-	A/ms
V_{CL}	clamping voltage	I_{CL} = 100 μ A; t_p = 1 ms; $T_j \le$ 125 °C; see Figure 13	650	-	-	V





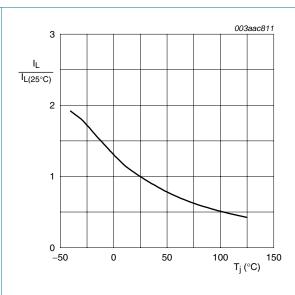
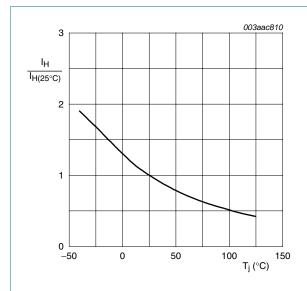
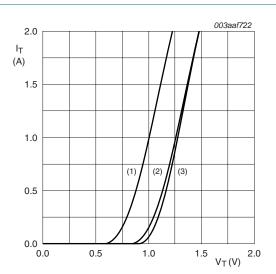


Fig 7. Normalized latching current as a function of junction temperature





 $V_o = 0.758 \, V$ $R_s = 0.263 \, \Omega$

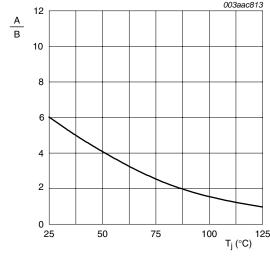
(1) $T_j = 125$ °C; typical values

(2) $T_j = 125$ °C; maximum values

(3) $T_j = 25$ °C; maximum values

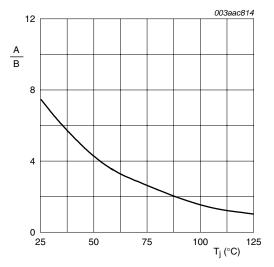
Fig 8. Normalized holding current as a function of junction temperature





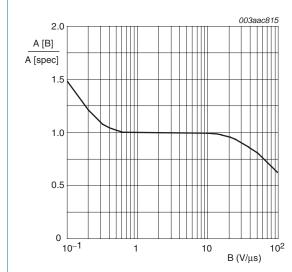
A is dV_D/dt at condition T_j °C B is dV_D/dt at condition T_i 125 °C

Fig 10. Normalized rate of rise of off-state voltage as a function of junction temperature



A is dI_{com}/dt at condition T_j °C B is dI_{com}/dt at condition T_j 125 °C $V_D = 400 \ V$

Fig 11. Normalized critical rate of rise of commutating current as a function of junction temperature



A[B] is dI_{com}/dt at condition B, dV_{com}/dt A[spec] is the specified data sheet value of dI_{com}/dt turn-off time < 20 ms

Fig 12. Normalized critical rate of change of commutating current as a function of critical rate of change of commutating voltage; minimum values

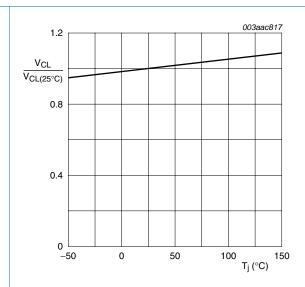
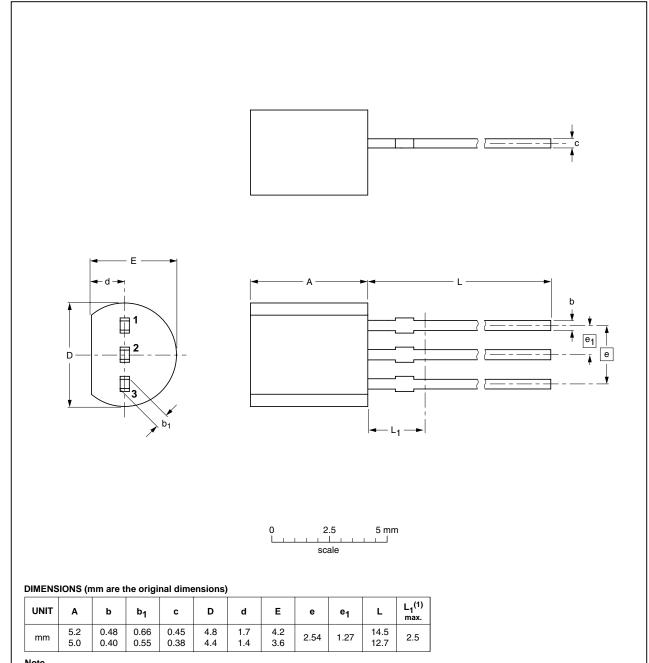


Fig 13. Normalized clamping voltage (upper limit) as a function of junction temperature; minimum values

Package outline

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	ENCES		EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEDEC JEITA PROJE		PROJECTION	ISSUE DATE
SOT54		TO-92	SC-43A			04-06-28 04-11-16

Fig 14. Package outline SOT54 (TO-92)

ACT108-600D

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
ACT108-600D v.2	20101227	Product data sheet	-	ACT108-600D v.1
Modifications:	 Status change 	d from preliminary to produc	t.	
	 Various chang 	es to content.		
ACT108-600D v.1	20100902	Preliminary data shee	t -	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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11. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications1
1.4	Quick reference data1
2	Pinning information
3	Ordering information
4	Limiting values3
5	Thermal characteristics6
6	Characteristics7
7	Package outline
8	Revision history11
9	Legal information12
9.1	Data sheet status
9.2	Definitions12
9.3	Disclaimers
9.4	Trademarks
10	Contact information 13

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